# **BTA312-600CT**

# 3Q Hi-Com Triac

Rev. 02 — 1 December 2010

Product data sheet

### 1. Product profile

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series CT" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber where "high junction operating temperature capability" is required.

#### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

### 1.3 Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; see Figure 4; see Figure 5	-	-	95	Α
Tj	junction temperature		-	-	150	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 126 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	12	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ C}}$	2	-	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ constant }}$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G-;$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 7}}{}$	2	-	35	mA

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N. 1
2	T2	main terminal 2	mb	T2 T1
3	G	gate		sym051
mb	T2	mounting base; main terminal 2	1 2 3	
			SOT78 (TO-220AB)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA312-600CT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 126 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	12	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	95	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	105	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	45	$A^2s$
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}$ ; $I_G = 0.2 \text{ A}$ ; $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

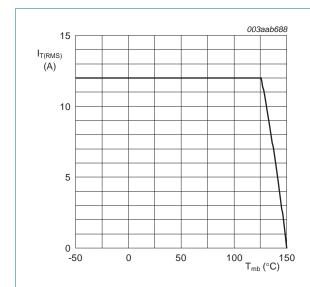
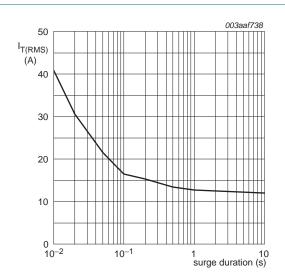
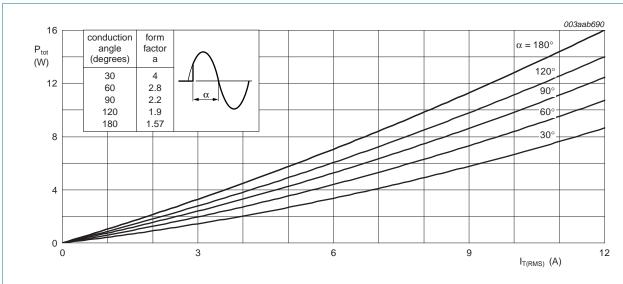


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



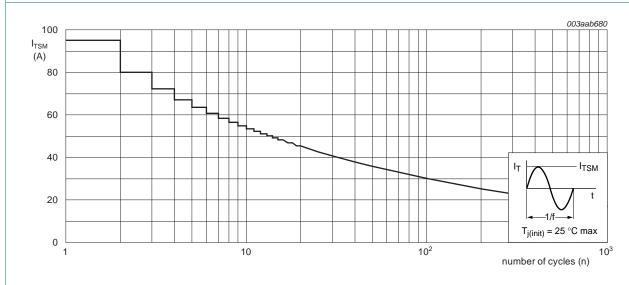
f = 50 Hz  $T_h$  = 126 °C

Fig 2. RMS on-state current as a function of surge duration; maximum values



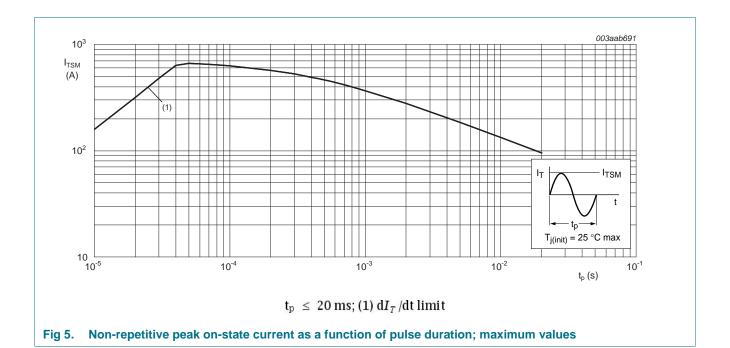
 $\alpha$  = conduction angle

Fig 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	full cycle; see Figure 6	-	-	1.5	K/W
	from junction to mounting base	half cycle; see Figure 6	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

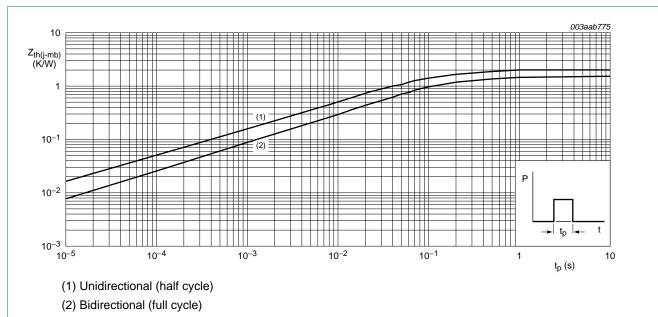


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	2	-	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 ^{\circ}\text{C; see } \frac{\text{Figure 7}}{}$	2	-	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	2	-	35	mA
lL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	50	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{}$	-	-	60	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2\text{- G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 8}}{}$	-	-	50	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; see <u>Figure 9</u>	-	-	35	mΑ
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	1.3	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	0.8	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ see Figure 11	0.25	-	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 150 °C	-	0.4	2	mΑ
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 150 °C; exponential waveform; gate open circuit	300	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s}; gate open circuit;}$ "without snubber" condition	8	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; gate open circuit}$	13	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 1 \text{ V}/\mu\text{s}; gate open circuit}$	20	-	-	A/ms
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

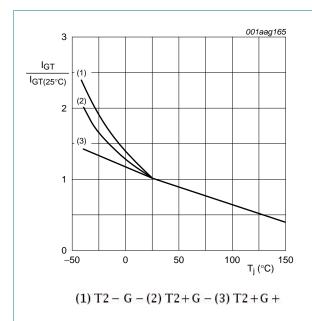


Fig 7. Normalized gate trigger current as a function of junction temperature

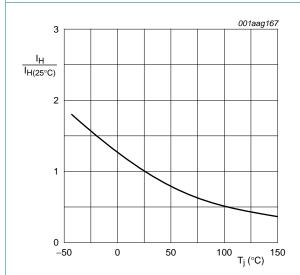


Fig 9. Normalized holding current as a function of junction temperature

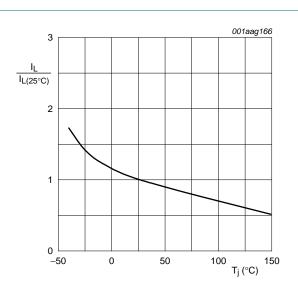
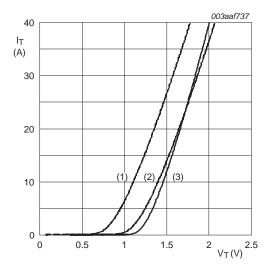


Fig 8. Normalized latching current as a function of junction temperature



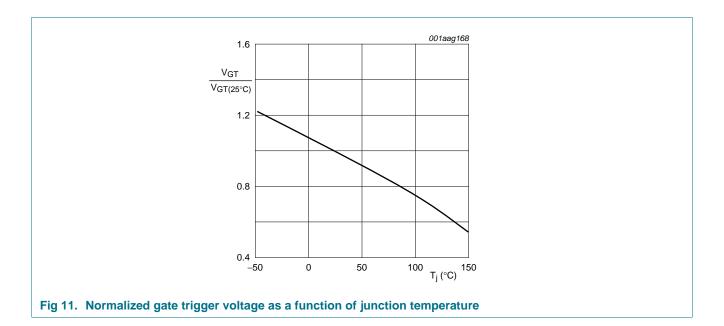
Vo = 1.127 V; Rs =  $0.027 \Omega$ 

(1) Tj = 150 °C; typical values

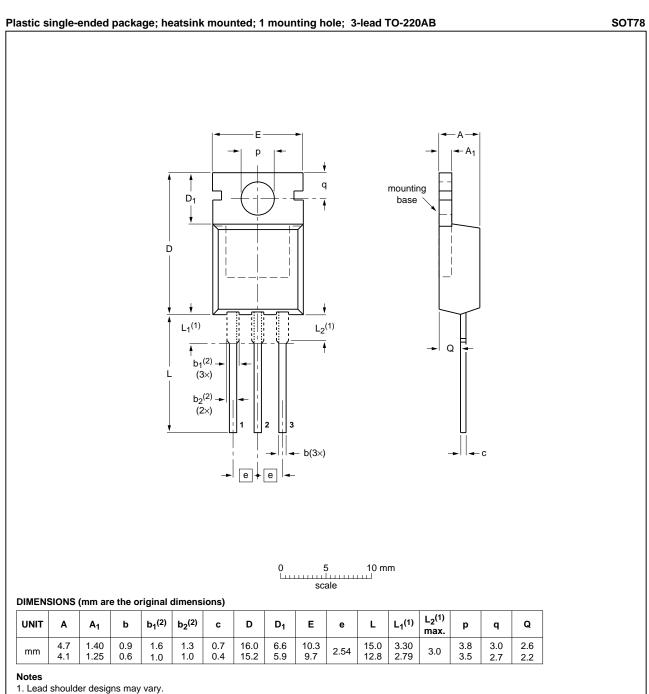
(2) Tj = 150 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage



## 7. Package outline



2. Dimension includes excess dambar.

OUTLINE		REFERENCES			EUROPEAN ISSUE DAT	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

Fig 12. Package outline SOT78 (TO-220AB)

BTA312-600CT

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## 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BTA312-600CT v.2	20101201	Product data sheet	-	BTA312_SER_CT_ET v.1	
Modifications: • Type number BTA312-600CT separated from data sheet BTA312_SER_CT_E					
<ul> <li>Various changes to content.</li> </ul>					
BTA312_SER_CT_ET v.1	20070406	Product data sheet	-	-	

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#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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